TOSHIBA Field Effect Transistor Silicon N Channel Junction Type

2SK192A

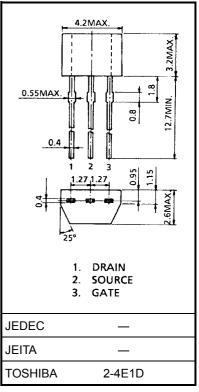
FM Tuner Applications VHF Band Amplifier Applications

- High power gain: GPS = 24dB (typ.) (f = 100 MHz)
- Low noise figure: NF = 1.8dB (typ.) (f = 100 MHz)
- High forward transfer admittance: $|Y_{fs}| = 7 \text{ mS (typ.)}$ (f = 1 kHz)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Gate-drain voltage	V_{GDO}	-18	V
Gate current	IG	10	mA
Drain power dissipation	P _D	200	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C

Unit: mm



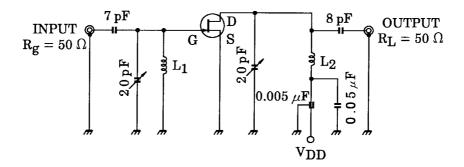
Weight: 0.13 g (typ.)

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = -1.0 \text{ V}, V_{DS} = 0$	_	_	-10	nA
Gate-drain breakdown voltage	V (BR) GDO	$I_G = -100 \mu A$	-18	_	_	V
Drain current	I _{DSS} (Note)	V _{GS} = 0, V _{DS} = 10 V	3	_	24	mA
Gate-source cut-off voltage	V _{GS} (OFF)	$V_{DS} = 10 \text{ V}, I_D = 1 \mu\text{A}$	-1.2	-3	_	V
Forward transfer admittance	Y _{fs}	$V_{GS} = 0$, $V_{DS} = 10 \text{ V}$, $f = 1 \text{ kHz}$	_	7	_	mS
Input capacitance	C _{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	3.5	_	pF
Reverse transfer capacitance	C _{rss}	$V_{GD} = -10 \text{ V}, f = 1 \text{ MHz}$	_	_	0.65	pF
Power gain	G _{PS}	V _{DD} = 10 V, f = 100 MHz (Figure 1)	_	24	_	dB
Noise figure	NF	V _{DD} = 10 V, f = 100 MHz (Figure 1)	_	1.8	3.5	dB

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Note: I_{DSS} classification Y: 3.0~7.0, GR: 6.0~14.0, BL: 12.0~24.0

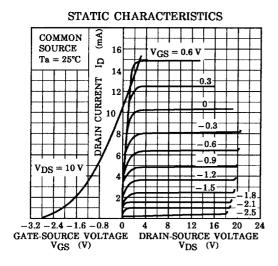


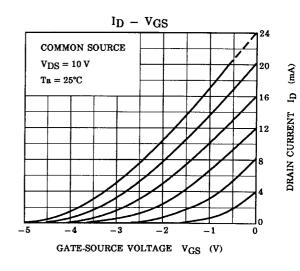
 $L_{1}\!\!:0.8$ mm/ A_{g} plated Cu wire 3 turns, 10 mm ID, 10 mm length

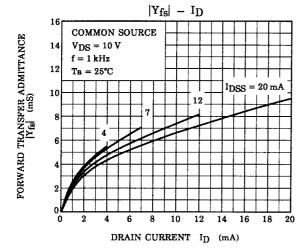
 $L_2{:}~0.8~\text{mm}\phi~A_g$ plated Cu wire 3.5 turns, 10 mm ID, 10 mm length

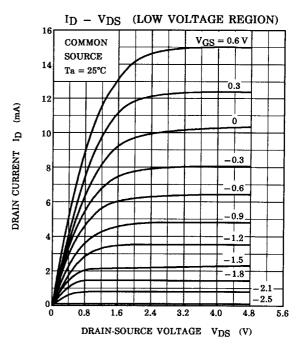
Figure 1 100 MHz G_{ps}, NF Test Circuit

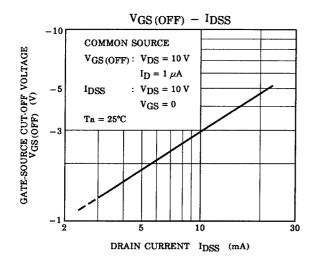
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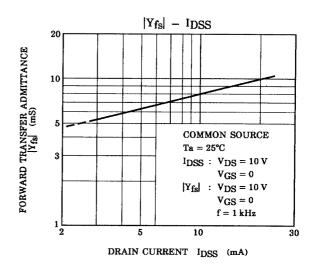




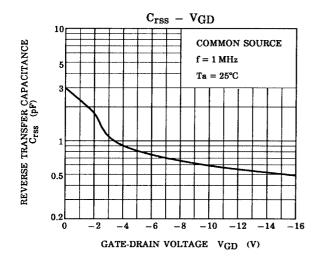


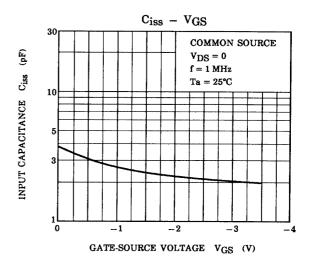


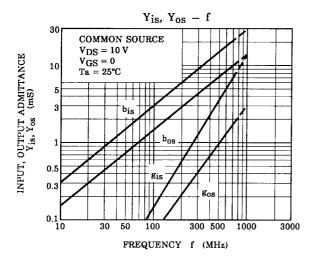


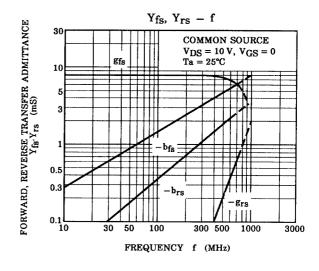


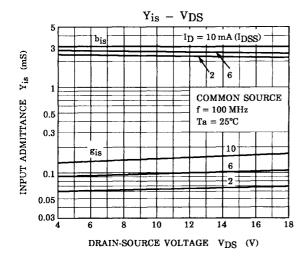
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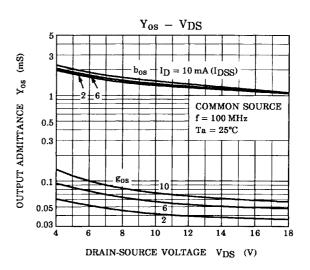




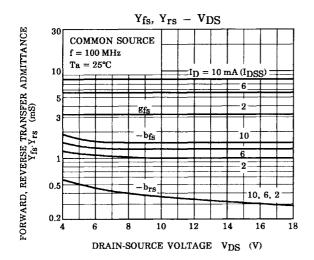


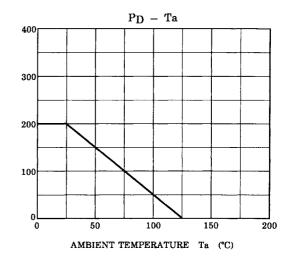






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